Woojin Jeon

List of Publications by Year in Descending Order

61 papers	1,320 citations	19 h-index	35 g-index
63 ext. papers	1,534 ext. citations	6.2 avg, IF	4.52 L-index

#	Paper	IF	Citations
61	Controlling the crystallinity of HfO2 thin film using the surface energy-driven phase stabilization and template effect. *Applied Surface Science*, **2022**, 590, 153082	6.7	
60	Chemistry of ruthenium as an electrode for metal-insulator-metal capacitor application. *Nanotechnology*, **2021**, 32, 045201	3.4	0
59	The Significance on Structural Modulation of Buffer and Gate Insulator for ALD Based InGaZnO TFT Applications. *IEEE Transactions on Electron Devices*, **2021**, 1-7	2.9	1
58	Y-doped HfO2 deposited by atomic layer deposition using a cocktail precursor for DRAM capacitor dielectric application. *Ceramics International*, **2021**, 48, 3236-3236	5.1	3
57	Improved Properties of the Atomic Layer Deposited Ru Electrode for Dynamic Random-Access Memory Capacitor Using Discrete Feeding Method. *ACS Applied Materials & Interfaces*, **2021**, 13, 23915-23927	9.5	0
56	Highly sustainable mechanical/electrical resistance switching behaviors via one-dimensional Ag/TiO2 core-shell resistive switchable materials in flexible composite. *Organic Electronics*, **2021**, 88, 105968	3.5	1
55	Modulation of the adsorption chemistry of a precursor in atomic layer deposition to enhance the growth per cycle of a TiO thin film. *Physical Chemistry Chemical Physics*, **2021**, 23, 2568-2574	3.6	0
54	An Empirical Investigation on the Effect of Oxygen Vacancy in ZrO Thin Film on the Frequency-Dependent Capacitance Degradation in the Metal-Insulator-Metal Capacitor. *IEEE Transactions on Electron Devices*, **2021**, 1-5	2.9	1
53	A visible-light phototransistor based on the heterostructure of ZnO and TiO with trap-assisted photocurrent generation.. *RSC Advances*, **2021**, 11, 12051-12057	3.7	4
52	Improving the photodetection and stability of a visible-light QDs/ZnO phototransistor via an Al2O3 additional layer. *Journal of Materials Chemistry C*, **2021**, 9, 2550-2560	7.1	4
51	Optimized Al-doped TiO2 gate insulator for a metal-oxide-semiconductor capacitor on a Ge substrate. *Journal of Materials Chemistry C*, **2021**, 9, 1572-1583	7.1	1
50	Investigating the interface characteristics of high-k ZrO2/SiO2 stacked gate insulator grown by plasma-enhanced atomic layer deposition for improving the performance of InSnZnO thin film transistors. *AIP Advances*, **2020**, 10, 015239	1.5	1
49	Modulated filamentary conduction of Ag/TiO2 core-shell nanowires to impart extremely sustained resistance switching behavior in a flexible composite. *Applied Materials Today*, **2020**, 19, 100569	6.6	7
48	Atomic layer deposition of Ru thin films using (2,4-dimethyloxopentadienyl)(ethylcyclopentadienyl)Ru and the effect of ammonia treatment during the deposition. *Journal of Materials Chemistry C*, **2020**, 8, 6993-7004	7.1	8
47	Recent advances in the understanding of high-k dielectric materials deposited by atomic layer deposition for dynamic random-access memory capacitor applications. *Journal of Materials Research*, **2020**, 35, 775-794	2.5	23
46	Improving the photoresponsivity and reducing the persistent photocurrent effect of visible-light ZnO/quantum-dot phototransistors via a TiO2 layer. *Journal of Materials Chemistry C*, **2020**, 8, 16384-16391	7.1	5
45	Sustainable resistance switching performance from composite-type ReRAM device based on carbon Nanotube@Titania core-shell wires. *Scientific Reports*, **2020**, 10, 18830	4.9	2

44	Comparative Study on the Gate-Induced Electrical Instability of p-Type SnO Thin-Film Transistors with SiO2 and Al2O3/SiO2 Gate Dielectrics. *Physica Status Solidi - Rapid Research Letters*, **2020**, 14, 2000304	2.5	1
43	Nanoscale surface engineering of a high-k ZrO2/SiO2 gate insulator for a high performance ITZO TFT via plasma-enhanced atomic layer deposition. *Journal of Materials Chemistry C*, **2020**, 8, 13342-13348	7.1	1
42	Substrate Effects on the Growth Behavior of Atomic-Layer-Deposited Ru Thin Films Using RuO4 Precursor and N2/H2 Mixed Gas. *Journal of Physical Chemistry C*, **2019**, 123, 22539-22549	3.8	5
41	The impact of plasma-enhanced atomic layer deposited ZrSiOx insulators on low voltage operated In-Sn-Zn-O thin film transistors. *Ceramics International*, **2019**, 45, 19166-19172	5.1	8
40	Scaling the Equivalent Oxide Thickness by Employing a TiO2 Thin Film on a ZrO2/Al2O3-Based Dielectric for Further Scaling of Dynamic Random Access Memory. *Physica Status Solidi - Rapid Research Letters*, **2019**, 13, 1900282	2.5	5
39	Improved performance and stability of In-Sn-Zn-O thin film transistor by introducing a meso-crystalline ZrO2 high-k gate insulator. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2019**, 37, 020924	2.9	10
38	Controlling the Current Conduction Asymmetry of HfO2 Metal–Insulator–Metal Diodes by Interposing Al2O3 Layer. *IEEE Transactions on Electron Devices*, **2019**, 66, 402-406	2.9	6
37	Optimization of a SiOx/SiNxOyCz multilayer structure for a reliable gas diffusion barrier via low-temperature plasma-enhanced atomic layer deposition. *Ceramics International*, **2019**, 45, 7407-7412	5.1	3
36	Controlling the Electrical Characteristics of ZrO2/Al2O3/ZrO2 Capacitors by Adopting a Ru Top Electrode Grown via Atomic Layer Deposition. *Physica Status Solidi - Rapid Research Letters*, **2019**, 13, 1800454	2.5	13
35	Quantitative Analysis of the Incorporation Behaviors of Sr and Ti Atoms During the Atomic Layer Deposition of SrTiO Thin Films. *ACS Applied Materials & Interfaces*, **2018**, 10, 8836-8844	9.5	15
34	Resistance Switching Capable Polymer Nanocomposites Employing Networks of One-Dimensional Nanocarbon Wrapped by TiO2 Conformal Layer. *IEEE Nanotechnology Magazine*, **2018**, 17, 567-573	2.6	0
33	Demonstrating the Ultrathin Metal–Insulator–Metal Diode Using TiN/ZrO2/Al2O3/ZrO2 Stack by Employing RuO2 Top Electrode. *IEEE Transactions on Electron Devices*, **2018**, 65, 660-666	2.9	12
32	Chemistry of SiNx thin film deposited by plasma-enhanced atomic layer deposition using di-isopropylaminosilane (DIPAS) and N2 plasma. *Ceramics International*, **2018**, 44, 20890-20895	5.1	6
31	Electrical Properties of ZrO2/Al2O3/ZrO2-Based Capacitors with TiN, Ru, and TiN/Ru Top Electrode Materials. *Physica Status Solidi - Rapid Research Letters*, **2018**, 12, 1800356	2.5	12
30	Wafer-Scale Synthesis of Reliable High-Mobility Molybdenum Disulfide Thin Films via Inhibitor-Utilizing Atomic Layer Deposition. *Advanced Materials*, **2017**, 29, 1703031	24	33
29	Depletion effect of polycrystalline-silicon gate electrode by phosphorus deactivation. *Solid-State Electronics*, **2017**, 127, 1-4	1.7	0
28	Physisorbed-precursor-assisted atomic layer deposition of reliable ultrathin dielectric films on inert graphene surfaces for low-power electronics. *2D Materials*, **2016**, 3, 035027	5.9	12
27	Frustration of Negative Capacitance in Al2O3/BaTiO3 Bilayer Structure. *Scientific Reports*, **2016**, 6, 19039	4.9	37

26	Vapor Transport Synthesis of Two-Dimensional SnS2 Nanocrystals Using a SnS2 Precursor Obtained from the Sulfurization of SnO2. *Crystal Growth and Design*, **2016**, 16, 3884-3889	3.5	19
25	Mesostructured HfxAlyO2 Thin Films as Reliable and Robust Gate Dielectrics with Tunable Dielectric Constants for High-Performance Graphene-Based Transistors. *ACS Nano*, **2016**, 10, 6659-66	16.7	15
24	Improved Initial Growth Behavior of SrO and SrTiO3 Films Grown by Atomic Layer Deposition Using {Sr(demamp)(tmhd)}2 as Sr-Precursor. *Chemistry of Materials*, **2015**, 27, 3881-3891	9.6	29
23	High-concentration boron doping of graphene nanoplatelets by simple thermal annealing and their supercapacitive properties. *Scientific Reports*, **2015**, 5, 9817	4.9	86
22	Reducing the nano-scale defect formation of atomic-layer-deposited SrTiO3 films by adjusting the cooling rate of the crystallization annealing of the seed layer. *Thin Solid Films*, **2015**, 589, 723-729	2.2	8
21	Interfacial charge-induced polarization switching in Al2O3/Pb(Zr,Ti)O3 bi-layer. *Journal of Applied Physics*, **2015**, 118, 224105	2.5	24
20	Asymmetry in electrical properties of Al-doped TiO2 film with respect to bias voltage. *Physica Status Solidi - Rapid Research Letters*, **2015**, 9, 410-413	2.5	9
19	High-throughput fabrication of infinitely long 10 nm slit arrays for terahertz applications. *Journal of Infrared, Millimeter, and Terahertz Waves*, **2015**, 36, 262-268	2.2	24
18	Controlling the Al-doping profile and accompanying electrical properties of rutile-phased TiO2 thin films. *ACS Applied Materials & Interfaces*, **2014**, 6, 7910-7	9.5	18
17	Structure and electrical properties of Al-doped HfO₂ and ZrO₂ films grown via atomic layer deposition on Mo electrodes. *ACS Applied Materials & Interfaces*, **2014**, 6, 22474-82	9.5	48
16	Grain size engineering for ferroelectric Hf0.5Zr0.5O2 films by an insertion of Al2O3 interlayer. *Applied Physics Letters*, **2014**, 105, 192903	3.4	134
15	Chemistry of active oxygen in RuOx and its influence on the atomic layer deposition of TiO2 films. *Journal of Materials Chemistry C*, **2014**, 2, 9993-10001	7.1	15
14	Ferroelectric properties and switching endurance of Hf0.5Zr0.5O2 films on TiN bottom and TiN or RuO2 top electrodes. *Physica Status Solidi - Rapid Research Letters*, **2014**, 8, 532-535	2.5	102
13	Evaluating the top electrode material for achieving an equivalent oxide thickness smaller than 0.4 nm from an Al-doped TiO₂ film. *ACS Applied Materials & Interfaces*, **2014**, 6, 21632-7	9.5	23
12	Highly improved uniformity in the resistive switching parameters of TiO2 thin films by inserting Ru nanodots. *Advanced Materials*, **2013**, 25, 1987-92	24	152
11	Titanium dioxide thin films for next-generation memory devices. *Journal of Materials Research*, **2013**, 28, 313-325	2.5	56
10	Atomic Layer Deposition of SrTiO3 Films with Cyclopentadienyl-Based Precursors for Metal–Insulator–Metal Capacitors. *Chemistry of Materials*, **2013**, 25, 953-961	9.6	61
9	32 × 32 Crossbar Array Resistive Memory Composed of a Stacked Schottky Diode and Unipolar Resistive Memory. *Advanced Functional Materials*, **2013**, 23, 1440-1449	15.6	136

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8	Resistive Memory: 32 □32 Crossbar Array Resistive Memory Composed of a Stacked Schottky Diode and Unipolar Resistive Memory (Adv. Funct. Mater. 11/2013). *Advanced Functional Materials*, **2013**, 23, 1350-1350	15.6	2
7	Controlling the initial growth behavior of SrTiO3 films by interposing Al2O3 layers between the film and the Ru substrate. *Journal of Materials Chemistry*, **2012**, 22, 15037		19
6	Growth of Conductive SrRuO3 Films by Combining Atomic Layer Deposited SrO and Chemical Vapor Deposited RuO2 Layers. *Chemistry of Materials*, **2012**, 24, 4686-4692	9.6	24
5	Impact of bimetal electrodes on dielectric properties of TiO2 and Al-doped TiO2 films. *ACS Applied Materials & Interfaces*, **2012**, 4, 4726-30	9.5	16
4	Optimization of chemical structure of Schottky-type selection diode for crossbar resistive memory. *ACS Applied Materials & Interfaces*, **2012**, 4, 5338-45	9.5	9
3	One-dimensional TiO□@Ag nanoarchitectures with interface-mediated implementation of resistance-switching behavior in polymer nanocomposites. *ACS Applied Materials & Interfaces*, **2012**, 4, 5727-31	9.5	18
2	TiO[sub 2]□Al[sub 2]O[sub 3]□TiO[sub 2] Nanolaminated Thin Films for DRAM Capacitor Deposited by Plasma-Enhanced Atomic Layer Deposition. *Electrochemical and Solid-State Letters*, **2008**, 11, H19		30
1	Nanosession: Atomic Layer Deposition419-428		